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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Applicants: Nayfeh et al.

Serial No.: 09/496,506

Filed: February 2, 2000

For: SILICON NANOPARTICLE
FIELD EFFECT TRANSISTOR AND
TRANSISTOR MEMORY DEVICE

Art Unit: 1741

) I hereby certify that this paper is being deposited with
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Registration No. 33132

Attorney for Applicant



INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In accordance with 37 C.F.R. §§1.56, 1.97 and 1.98, applicants through counsel

herewith:

Submit copies of the patents set forth in the attached form PTO-1449 as

follows:

PUBLICATIONS

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Applicants respectfully request that the Examiner consider the above-listed references in the examination of this application and list these references of record in the application.

Respectfully submitted,

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